

32,768-WORD BY 8-BIT STATIC RAM

DESCRIPTION

The TC55257DPI/DFI/DFTI/DTRI is a 262,144-bit static random access memory (SRAM) organized as 32,768 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 5 V ± 10% power supply. Advanced circuit technology provides both high speed and low power at an operating current of 5 mA/MHz (typ) and a minimum cycle time of 70 ns. It is automatically placed in low-power mode at 0.3 μA standby current (typ) when chip enable (CE) is asserted high. There are two control inputs. \overline{CE} is used to select the device and for data retention control, and output enable (\overline{OE}) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. And, with a guaranteed operating range of - 40° to 85°C, the TC55257DPI/DFI/DFTI/DTRI can be used in environments exhibiting extreme temperature conditions. The TC55257DPI/DFI/DFTI/DTRI is available in a plastic 28-pin dual-in-line package (DIP), plastic 28-pin small-outline package (SOP) and normal and reverse pinout plastic 28-pin thin-small-outline package (TSOP).

FEATURES

- Low-power dissipation
Operating: 27.5 mW/MHz (typical)
- Standby current of 2 μA (maximum) at $T_a = 25^\circ\text{C}$
- Single power supply voltage of 5 V ± 10%
- Power down features using CE.
- Data retention supply voltage of 2 to 5.5 V
- Direct TTL compatibility for all inputs and outputs
- Wide operating temperature range of - 40° to 85°C

● Access Times (maximum):

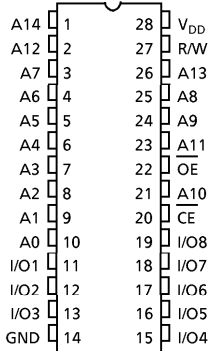
	TC55257DPI/DFI/DFTI/DTRI	
	-70L	-85L
Access Time	70 ns	85 ns
\overline{CE} Access Time	70 ns	85 ns
\overline{OE} Access Time	35 ns	45 ns

● Packages:

- DIP28-P-600-2.54 (DPI) (Weight: 4.42 g typ)
- SOP28-P-450-1.27 (DFI) (Weight: 0.79 g typ)
- TSOP I 28-P-0.55 (DFTI) (Weight: 0.22 g typ)
- TSOP I 28-P-0.55A (DTRI) (Weight: 0.22 g typ)

PIN ASSIGNMENT (TOP VIEW)

○ 28 PIN DIP & SOP

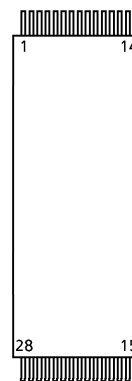


○ 28 PIN TSOP

(Normal pinout)



(Reverse pinout)



PIN NAMES

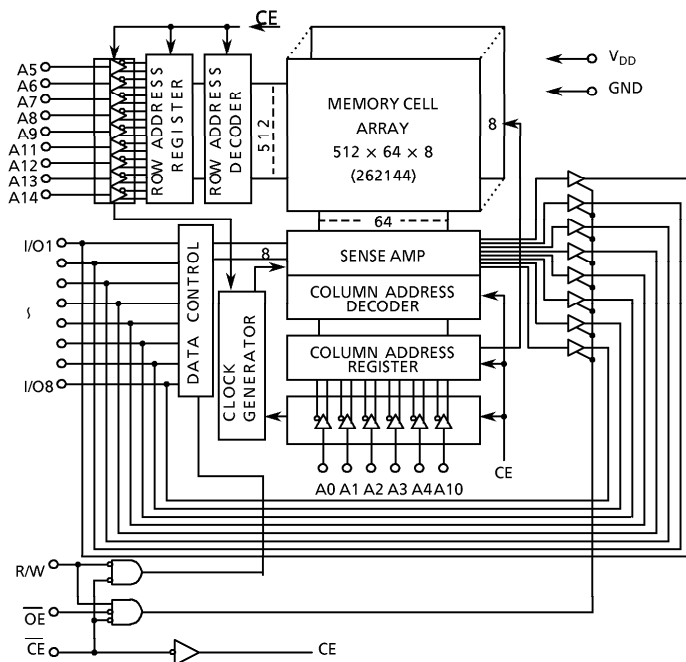
A0 to A14	Address Input
R/W	Read/Write Control
\overline{OE}	Output Enable
CE	Chip Enable
I/O1 to I/O8	Data Input/Output
V _{DD}	Power (+ 5 V)
GND	Ground

PIN NO.	1	2	3	4	5	6	7	8	9	10	11	12	13	14
PIN NAME	\overline{OE}	A ₁₁	A ₉	A ₈	A ₁₃	R/W	V _{DD}	A ₁₄	A ₁₂	A ₇	A ₆	A ₅	A ₄	A ₃
PIN NO.	15	16	17	18	19	20	21	22	23	24	25	26	27	28
PIN NAME	A ₂	A ₁	A ₀	I/O1	I/O2	I/O3	GND	I/O4	I/O5	I/O6	I/O7	I/O8	\overline{CE}	A ₁₀

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BLOCK DIAGRAM



OPERATION MODE

MODE	\overline{CE}	\overline{OE}	R/W	I/O1 to I/O8	POWER
Read	L	L	H	D _{OUT}	I _{DDO}
Write	L	x	L	D _{IN}	I _{DDO}
Outputs Disabled	L	H	H	High-Z	I _{DDO}
Standby	H	x	x	High-Z	I _{DDs}

Note: x = don't care. H = logic high. L = logic low.

ABSOLUTE MAXIMUM VALUES

SYMBOL	RATING	VALUE	UNIT
V _{DD}	Power Supply Voltage	- 0.3 to 7.0	V
V _{IN}	Input Voltage	- 0.3* to 7.0	V
V _{IO}	Input/Output Voltage	- 0.5* to V _{DD} + 0.5	V
P _D	Power Dissipation	1.0/0.6**	W
T _{solder}	Soldering Temperature (10 s)	260	°C
T _{strg}	Storage Temperature	- 55 to 150	°C
T _{opr}	Operating Temperature	- 40 to 85	°C

* - 3.0 V when measured at a pulse width of 50 ns

** SOP

DC RECOMMENDED OPEVALUE CONDITIONS (Ta = - 40° to 85°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V _{DD}	Power Supply Voltage	4.5	5.0	5.5	V
V _{IH}	Input High Voltage	2.4	-	V _{DD} + 0.3	
V _{IL}	Input Low Voltage	- 0.3*	-	0.6	
V _{DH}	Data Retention Supply Voltage	2.0	-	5.5	

* - 3.0 V when measured at a pulse width of 50 ns

DC CHARACTERISTICS (Ta = - 40° to 85°C, V_{DD} = 5 V ± 10%)

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT	
I _{IL}	Input Leakage Current	V _{IN} = 0 V to V _{DD}	-	-	± 1.0	μA	
I _{OH}	Output High Current	V _{OH} = 2.4 V	- 1.0	-	-	mA	
I _{OL}	Output Low Current	V _{OL} = 0.4 V	4.0	-	-	mA	
I _{LO}	Output Leakage Current	C _E = V _{IH} or R/W = V _{IL} or \overline{OE} = V _{IH} V _{OUT} = 0 V to V _{DD}	-	-	± 1.0	μA	
I _{DDO1}	Operating Current	C _E = V _{IL} R/W = V _{IH} , I _{OUT} = 0 mA Other Inputs = V _{IH} /V _{IL}	t _{cycle} = 1 μs	-	10	-	mA
			t _{cycle} = min	-	-	70	
I _{DDO2}	Operating Current	C _E = 0.2 V R/W = V _{DD} - 0.2 V, I _{OUT} = 0 mA Other Inputs = V _{DD} - 0.2 V, 0.2 V	t _{cycle} = 1 μs	-	5	-	mA
			t _{cycle} = min	-	-	60	
I _{DDS1}	Standby Current	C _E = V _{IH}	-	-	3	mA	
I _{DDS2}		C _E = V _{DD} - 0.2 V V _{DD} = 2.0 to 5.5 V	Ta = - 40° to 85°C	-	-	30	μA
			Ta = 25°C	-	0.3	2	

CAPACITANCE (Ta = 25°C, f = 1 MHz)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C _{IN}	Input Capacitance	V _{IN} = GND	10	pF
C _{OUT}	Output Capacitance	V _{OUT} = GND	10	pF

Note: This parameter is periodically sampled and is not 100% tested.

AC CHARACTERISTICS AND OPERATING CONDITIONS ($T_a = -40^\circ$ to 85°C , $V_{DD} = 5\text{ V} \pm 10\%$)READ CYCLE

SYMBOL	PARAMETER	TC55257DPI/DFI/DFTI/DTRI				UNIT
		-70L		-85L		
		MIN	MAX	MIN	MAX	
t_{RC}	Read Cycle Time	70	–	85	–	ns
t_{ACC}	Address Access Time	–	70	–	85	
t_{CO}	Chip Enable Access Time	–	70	–	85	
t_{OE}	Output Enable Access Time	–	35	–	45	
t_{COE}	Chip Enable Low to Output Active	5	–	5	–	
t_{OEE}	Output Enable Low to Output Active	0	–	0	–	
t_{OD}	Chip Enable High to Output High-Z	–	25	–	30	
t_{ODO}	Output Enable High to Output High-Z	–	25	–	30	
t_{OH}	Output Data Hold Time	10	–	10	–	

WRITE CYCLE

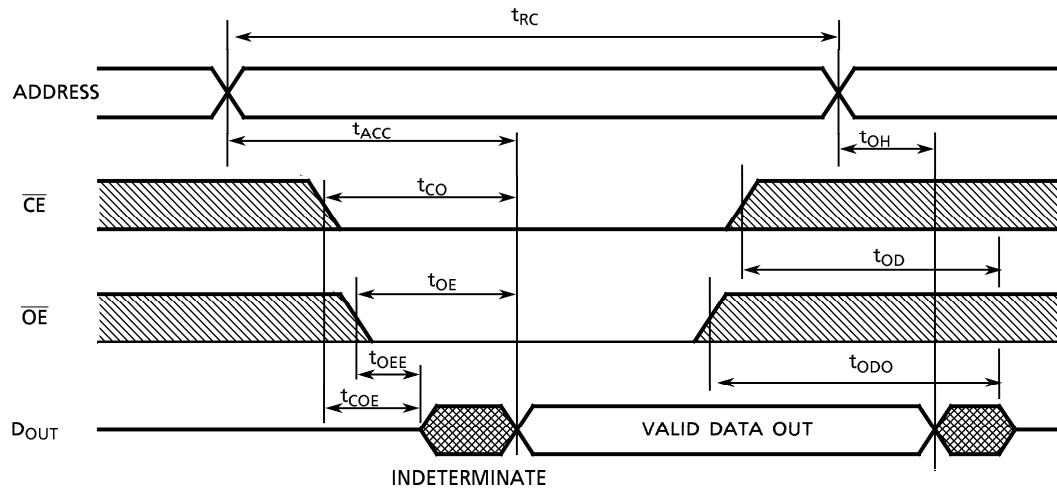
SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL				UNIT
		-70L		-85L		
		MIN	MAX	MIN	MAX	
t_{WC}	Write Cycle Time	70	–	85	–	ns
t_{WP}	Write Pulse Width	50	–	60	–	
t_{CW}	Chip Enable to End of Write	60	–	65	–	
t_{AS}	Address Setup Time	0	–	0	–	
t_{WR}	Write Recovery Time	0	–	0	–	
t_{ODW}	R/W Low to Output High-Z	–	25	–	30	
t_{OEW}	R/W High to Output Active	0	–	0	–	
t_{DS}	Data Setup Time	30	–	40	–	
t_{DH}	Data Hold Time	0	–	0	–	

AC TEST CONDITIONS

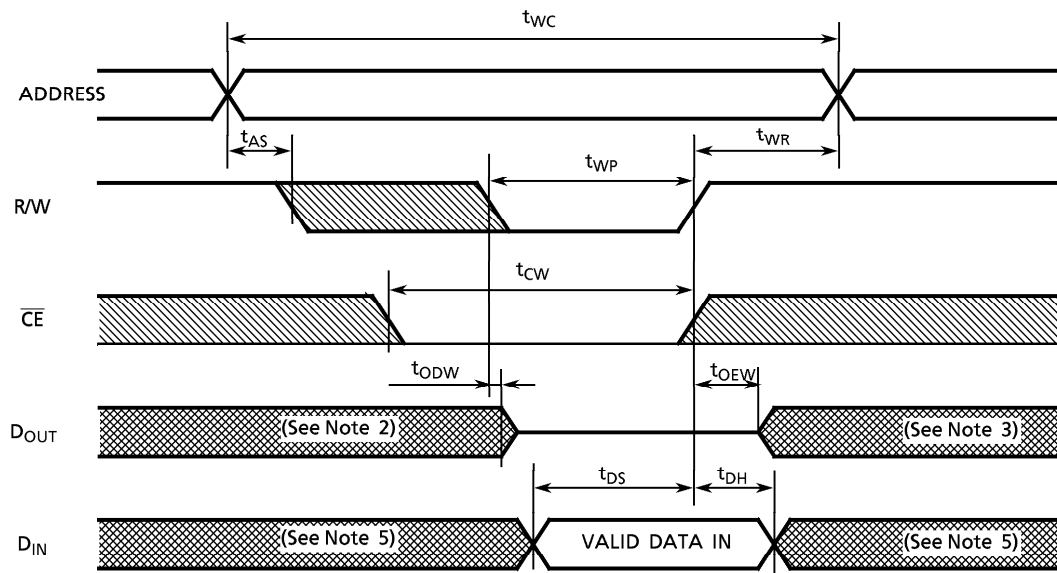
Output load: 100 pF + one TTL gate
 Input pulse level: 0.4 V, 2.6 V
 Timing measurements: 1.5 V
 ReferenChip Enable level: 1.5 V
 t_R, t_F : 5 ns

TIMING DIAGRAMS

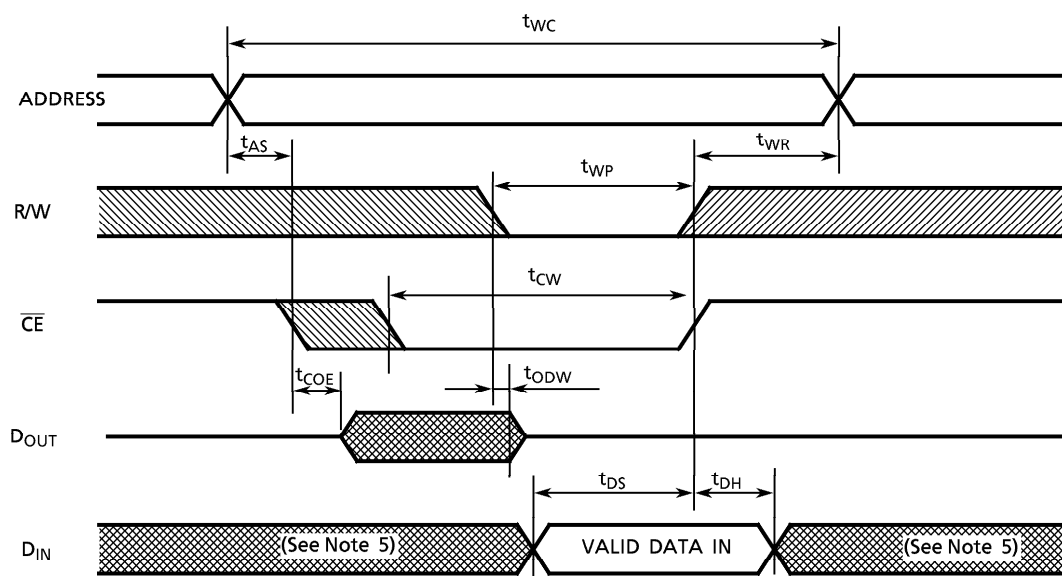
READ CYCLE (See Note 1)



WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)



WRITE CYCLE 2 (\overline{CE} CONTROLLED) (See Note 4)



Note: (1) R/W remains HIGH for the read cycle.

- (2) If \overline{CE} goes LOW coincident with or after R/W goes LOW, the outputs will remain at high impedance.
- (3) If \overline{CE} goes HIGH coincident with or before R/W goes HIGH, the outputs will remain at high impedance.
- (4) If \overline{OE} is HIGH during the write cycle, the outputs will remain at high impedance.
- (5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

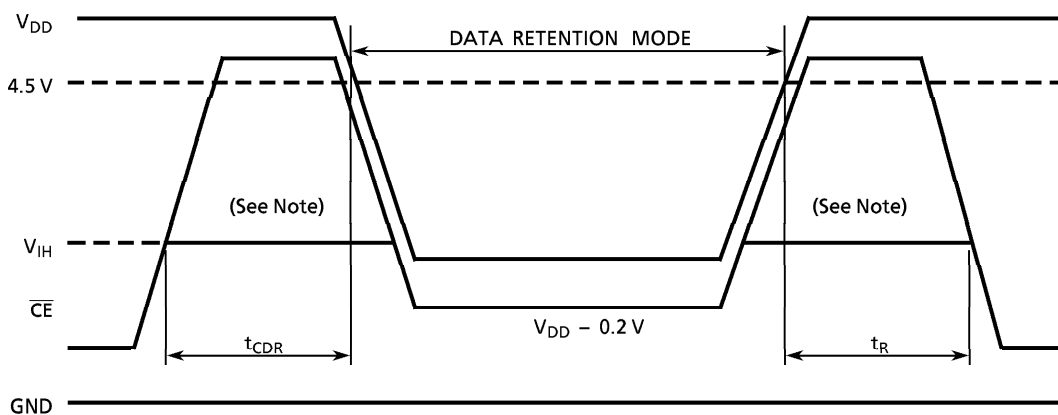
DATA RETENTION CHARACTERISTICS (Ta = - 40° to 85°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V _{DH}	Data Retention Supply Voltage	2.0	-	5.5	V
I _{DD52}	Standby Current	V _{DH} = 3.0 V	-	15*	μA
		V _{DH} = 5.5 V	-	30	μA
t _{CDR}	Chip Deselect to Data Retention Mode Time	0	-	-	
t _R	Recovery Time	t _{RC} (See Note)	-	-	ns

* 2 μA (max) at Ta = - 40° to 40°C

Note: Read cycle time.

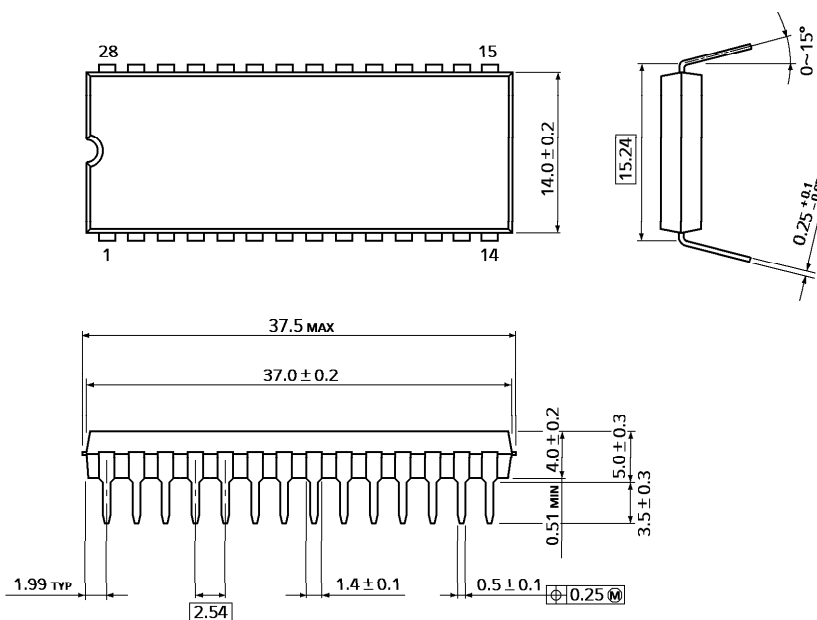
CE CONTROLLED DATA RETENTION MODE



Note: When CE is operating at the V_{IH} level (2.4 V), the standby current is given by I_{DD51} during the transition of V_{DD} from 4.5 to 2.6 V.

PACKAGE DIMENSIONS (DIP28-P-600-2.54)

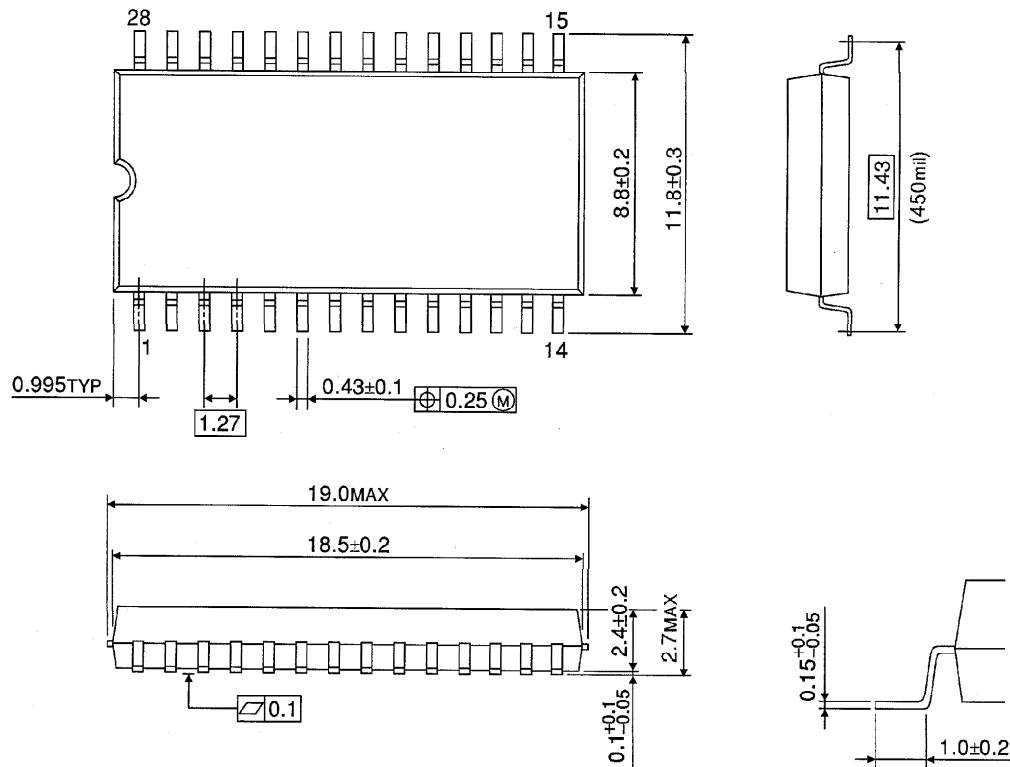
Units in mm



Weight: 4.42 g (typ)

PACKAGE DIMENSIONS (SOP28-P-450-1.27)

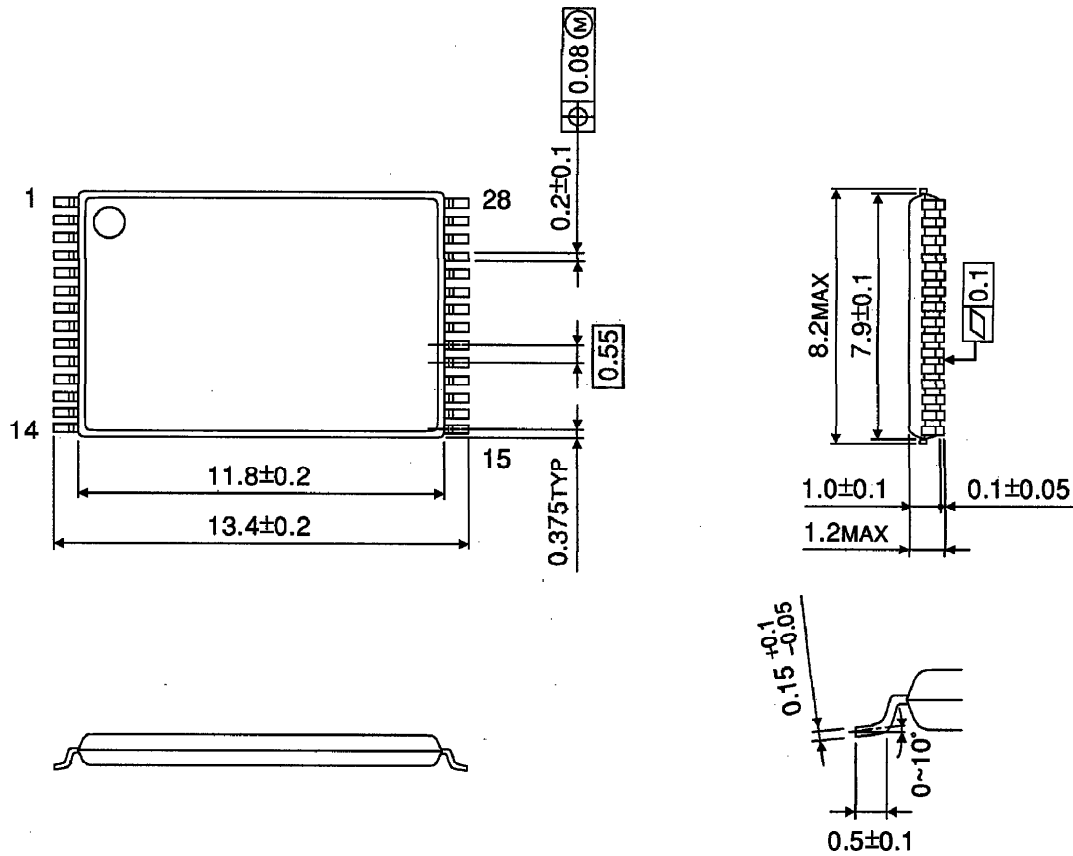
Units in mm



Weight: 0.79 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55)

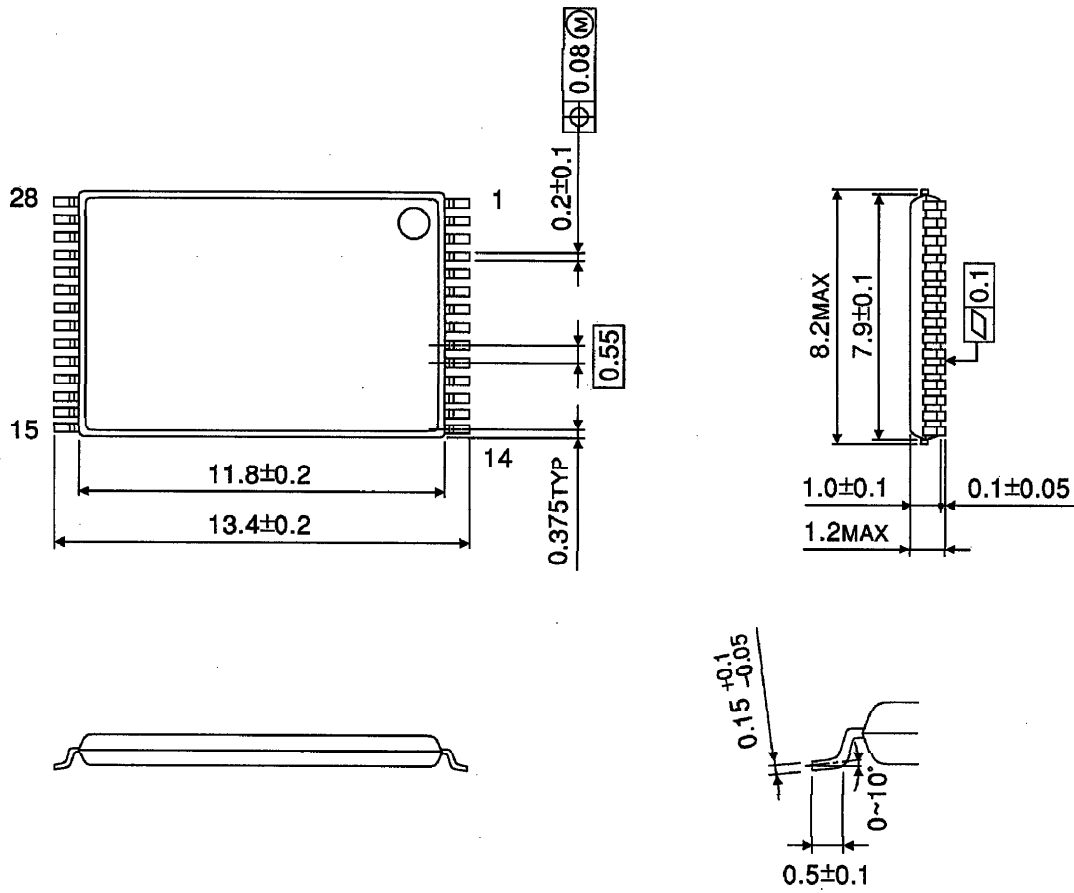
Units in mm



Weight: 0.22 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55A)

Units in mm



Weight: 0.22 g (typ)